NSN 5961-01-476-2270

Diode Semiconductor Device - Page 1 of 1

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Voltage Rating In Volts Per Characteristic:

6.12 reverse breakdown voltage, instantaneous and 7.48 reverse breakdown voltage, instantaneous

Current Rating Per Characteristic:

10.00 milliamperes drain current pascal

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius ambient air

Special Features:

Diode is a 5 amp - 580 watt bipolar transient suppressor, dual die; each die is glass passivated; metalization material is nickel and gold plated (ni-ni-au); standoff voltage (vso) 5.50 volts; max. Reverse leakage (ir) at vso is 600 microamps (limit is doubled when reverse breakdown voltage is 10 volts or less); max. Clamping voltage (vcl) 10.8 volts at peak pulse current (ipp) 53.0 amps

Precious Material And Location:

Plating gold

Precious Material:

Gold

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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